TOSHIBA

TOSHIBA HIGH EFFICIENCY RECTIFIER SILICON EPITAXIAL TYPE

5 D L Z 4 7 A

SWITCHING TYPE POWER SUPPLY APPLICATION

CONVERTER & CHOPPER APPLICATION

• Repetitive Peak Reverse Voltage : V_{RRM}=200V

• Average Output Rectified Current : IO=5A

• Ultra Fast Reverse-Recovery Time : t_{rr}=35ns (Max.)

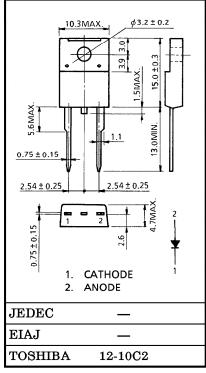
• Low Forward Voltage : V_{FM}=0.98V

Low Switching Losses and Low Output Noise.

MAXIMUM RATINGS

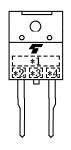
CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	v_{RRM}	200	V	
Average Output Rectified Current	I_{O}	5	Α	
Peak One Cycle Surge Forward	T	50 (50Hz)		
Current (Non-Repetitive)	tive) IFSM		A	
Junction Temperature	T_{j}	-40~150	°C	
Storage Temperature Range	$ m T_{stg}$	-40~150	°C	
Screw Torque		0.6	N∙m	

Unit in mm



Weight: 2.0g

MARKING



*1	MARK	5DLZ47	TYPE	5DLZ47A		
*2	A					
*3	Polarity		←			
*4	Lot Number Month (Starting from Alphabet A) Year (Last Number of the Christian Era)					

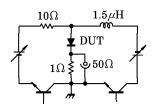
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[●] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

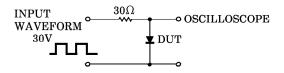
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Peak Forward Voltage	${ m v_{FM}}$	$I_{\text{FM}} = 5A$	_	0.98	V
Repetitive Peak Reverse Current	$I_{ m RRM}$	$V_{ m RRM}$ =200V	1	10	μ A
Reverse Recovery Time (Note 1)	$ m t_{rr}$	$I_F = 2A$, di/dt = $-20A/\mu s$	_	35	ns
Forward Recovery Time (Note 2)	t_{fr}	$I_{\mathbf{F}} = 1A$	_	100	ns
Thermal Resistance	R _{th (j-c)}	DC	_	4.0	°C/W

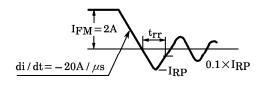
Note 1: t_{rr} TEST CIRCUIT



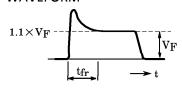
Note 2: tfr TEST CIRCUIT



t_{rr} WAVEFORM



tfr WAVEFORM



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